

# **RENESAS** HAF1001-90 & HAF1001-90E alternative



Silicon P-Channel 60-V MOS FET Series Power Switching



PRODUCT SUMMARY		
V <sub>DS</sub>	-60	V
R <sub>DS(on)</sub> V <sub>GS</sub> = 10 V	62	mΩ
$R_{DS(on)}$ $V_{GS} = 4.5 \text{ V}$	74	mΩ
I <sub>D</sub>	-40	Α
Configuration	Sin	gle

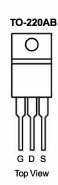
# **FEATURES**

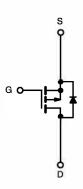
- TrenchFET® Power MOSFET
- 100 % UIS Tested



# **APPLICATIONS**

· Load Switch





P-Channel MOSFET

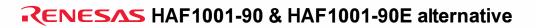
ABSOLUTE MAXIMUM RATINGS $T_C =$	25 °C, unless othe	rwise noted		
Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current (T, = 175 °C)	T <sub>C</sub> = 25 °C	I <sub>D</sub>	-40	
Continuous Brain Current (1) = 175 C)	T <sub>C</sub> = 100 °C	ן טי ן	-30	A
Pulsed Drain Current	•	I <sub>DM</sub>	- 90	Α
Continuing Source Current (Diode Conduction)		Is	- 30	
Avalanche Current		I <sub>AS</sub>	- 28	
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	7.2	mJ
Mayimum Dayar Dissination	T <sub>C</sub> = 25 °C	P <sub>D</sub>	60 <sup>a</sup>	w
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	'B	2 <sup>b</sup>	1 "
Operating Junction and Storage Temperature Range	*	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient <sup>b</sup>	t ≤ 10 sec	R <sub>thJA</sub>	20	25		
	Steady State	' 'thJA	62	75	°C/W	
Junction-to-Case		R <sub>thJC</sub>	5	6		

### Notes:

- a. See SOA curve for voltage derating.
- b. Surface Mounted on 1" x 1" FR-4 boad.

more info: sales@bec.co.uk www.bec.co.uk



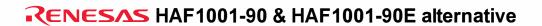


Parameter	Symbol	Test Conditions	Min	Typ <sup>a</sup>	Max	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 60			v	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V			- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			- 50	μΑ	
		V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			- 150		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 10			Α	
Drain-Source On-State Resistance <sup>b</sup>		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5 A		62			
	_	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5 A, T <sub>J</sub> = 125 °C		80			
	r <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5 A, T <sub>J</sub> = 175 °C		110		mΩ	
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 2 A		74		s	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 5 A		8		S	
Dynamic							
Input Capacitance	C <sub>iss</sub>			1300		S pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		120			
Reverse Transfer Capacitance	C <sub>rss</sub>			90			
Total Gate Charge	Qg			13			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -8.4 \text{ A}$		2.3		nC	
Gate-Drain Charge	Q <sub>gd</sub>			3.2		pF nC	
Gate Resistance	R <sub>g</sub>	f = 1 MHz		8.0		Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			5	10		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -30 \text{ V, R}_{L} = 3.57 \Omega$		14	25		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong -8.4 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 2.5 \Omega$		15	25	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			7	12		
Source-Drain Diode Ratings and Cha	aracteristics	(T <sub>C</sub> = 25 °C) <sup>b</sup>					
Pulsed Current	I <sub>SM</sub>			- 20		Α	
Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 2 A, V <sub>GS</sub> = 0 V		- 0.9	- 1.3	٧	
Reverse Recovery Time	t <sub>rr</sub>	1 9 A di/dt 100 A/::-		50	80	ns	
Reverse Recovery Time	Q <sub>rr</sub>	- I <sub>F</sub> = - 8 A, di/dt = 100 A/μs		80	120	nC	

#### Notes:

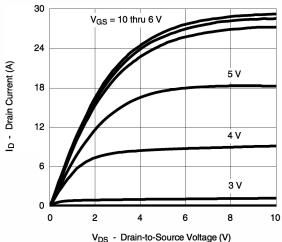
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



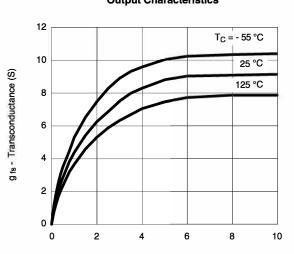


### TYPICAL CHARACTERISTICS 25 °C unless noted

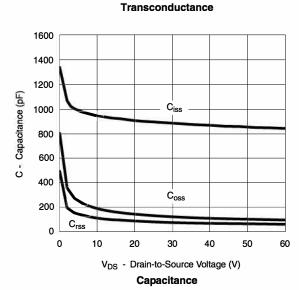


V<sub>DS</sub> - Drain-to-Source Voltage (V)

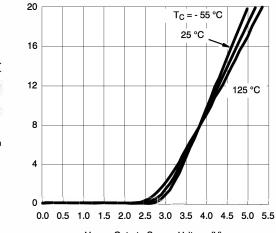
Output Characteristics



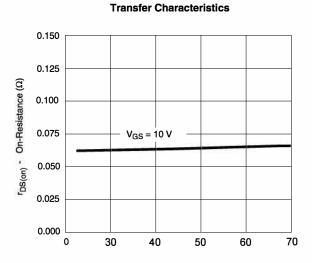
I<sub>D</sub> - Drain Current (A)



lo - Drain Current (A)

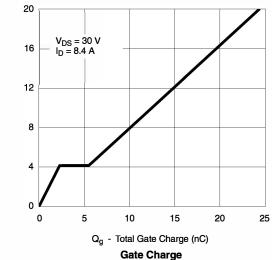


V<sub>GS</sub> - Gate-to-Source Voltage (V)



ID - Drain Current (A)





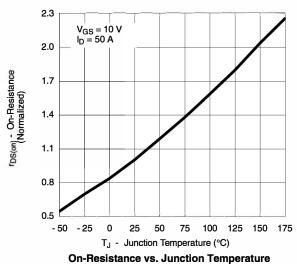
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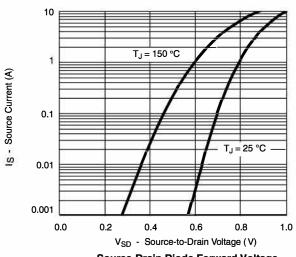
VGS - Gate-to-Source Voltage (V)

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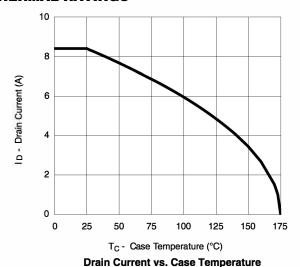
#### TYPICAL CHARACTERISTICS 25 °C unless noted



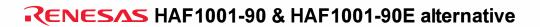


Source-Drain Diode Forward Voltage

# THERMAL RATINGS

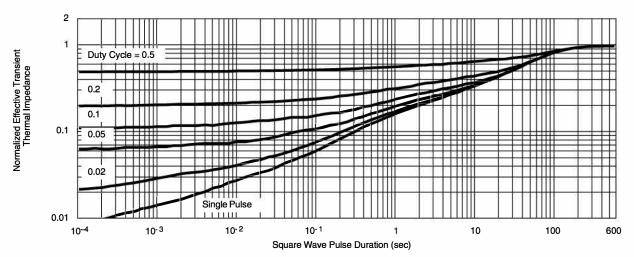


 $\begin{array}{c} 100 \\ 10 \\ \times \text{Limited by } \text{r}_{DS(on)} \\ 1 \\ 0.01 \\ 0.01 \\ \text{O} \\ \text{O$ 

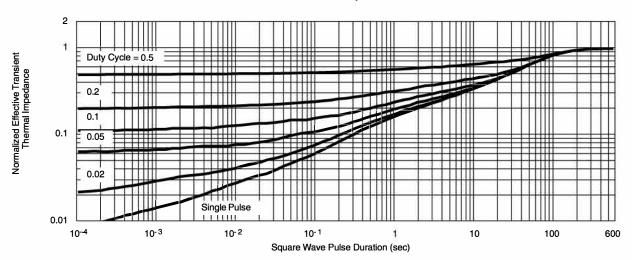




### THERMAL RATINGS



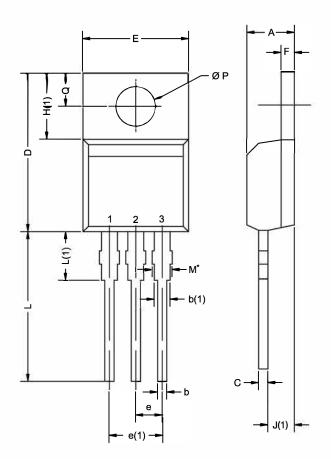
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



# **TO-220AB**



	MILLIM	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
E	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØР	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
CN: X12-	0208-Rev. N, 1	08-Oct-12			

# Notes

 $<sup>^{\</sup>star}$  M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM

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